

μPA2660T1R

DUAL N-CHANNEL MOSFET 20 V, 4.0 A, 42 m Ω

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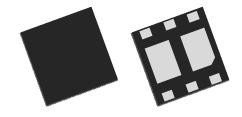
Description

The μ PA2660T1R is Dual N-channel MOS Field Effect Transistors for switching application.

This device features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

Features

- DS MAXIMUM RATINGS $20V(T_A = 25^{\circ}C)$
- 2.5V drive available
- Low on-state resistance
 - $R_{DS \text{ (on)}1} = 42 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = 4.5 \text{ V}$, $I_D = 2.0 \text{ A}$)
 - $R_{DS (on)2} = 62 \text{ m}\Omega \text{ MAX}. (V_{GS} = 2.5 \text{ V}, I_D = 2.0 \text{ A})$
- Built-in gate protection diode
- Lead-free and Halogen-free



6pinHUSON2020(Dual)

Ordering Information

Part Number	Package		
μPA2660T1R-E2-AX*1	6pinHUSON2020(Dual)		

Note: *1.Pb-free (This product does not contain Pb in the external electrode and other parts.)

Absolute Maximum Ratings ($T_A = 25$ °C)

Item	Symbol	Ratings	Unit
Drain to Source Voltage (V _{GS} = 0 V)	V_{DSS}	20	V
Gate to Source Voltage (V _{DS} = 0 V)	V_{GSS}	±12	V
Drain Current (DC)	I _{D(DC)}	±4.0	Α
Drain Current (pulse) *1	I _{D(pulse)}	±16	Α
Total Power Dissipation (1 unit, 5 s) *2	P _{T1}	1.5	W
Total Power Dissipation (2 units, 5 s) *2	P _{T2}	2.3	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{STG}	-55 to +150	°C

Notes: *1. PW≤10 μs, Duty Cycle≤1%

Caution: This product is electrostatic-sensitive device due to low ESD capability and should be handled with caution for electrostatic discharge.

 $V_{ESD} = \pm 400 V \text{ MIN.} (C = 100 pF, R = 1.5 K\Omega)$

^{*2.} Mounted on glass epoxy board of 25.4mm x 25.4mm x 0.8mmt

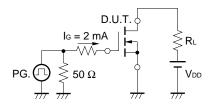
Electrical Characteristics (T_A = 25°C)

Characteristics	Symbol	MIN.	TYP.	MAX.	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			1.0	μA	V _{DS} = 20 V, V _{GS} = 0 V
Gate Leakage Current	I _{GSS}			±10	μA	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0 \text{ V}$
Gate Cut-off Voltage	V _{GS(off)}	0.5		1.5	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$
Forward Transfer Admittance *1	y _{fs}	5.0			S	$V_{DS} = 10 \text{ V}, I_{D} = 2.0 \text{ A}$
Drain to Source On-state	R _{DS(on)1}		33	42	mΩ	V_{GS} = 4.5 V, I_{D} = 2.0 A
Resistance *1	R _{DS(on)2}		43	62	mΩ	$V_{GS} = 2.5 \text{ V}, I_D = 2.0 \text{ A}$
Input Capacitance	C _{iss}		330		pF	$V_{DS} = 10 \text{ V}, V_{GS} = 0 \text{ V},$
Output Capacitance	Coss		66		pF	f = 1.0 MHz
Reverse Transfer Capacitance	C _{rss}		38		pF	
Turn-on Delay Time	t _{d (on)}		12		ns	I_D = 2.0 A, V_{DD} = 10 V, V_{GS} = 4.5 V, R_G = 6 Ω
Rise Time	t _r		6.4		ns	
Turn-off Delay Time	t _{d (off)}		27		ns	
Fall Time	t _f		6.6		ns	
Total Gate Charge	Q_G		4.5		nC	I _D = 4.0 A , V _{DD} = 16 V, V _{GS} = 10 V
Gate to Source Charge	Q _{GS}		1.0		nC	
Gate to Drain Charge	Q_{GD}		1.5		nC	
Body Diode Forward Voltage *1	V _{F(S-D)}			1.5	V	I _F = 4.0 A, V _{GS} = 0 V

Note: *1. Pulsed

TEST CIRCUIT 1 SWITCHING TIME

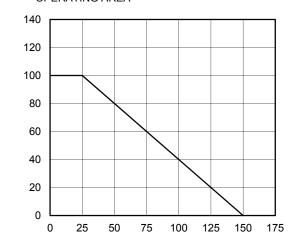
TEST CIRCUIT 2 GATE CHARGE



dT - Percentage of Rated Power - %

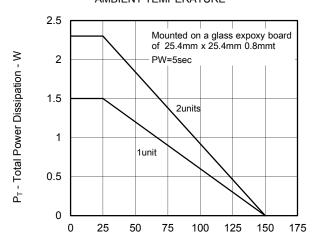
Typical Characteristics ($T_A = 25$ °C)

DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



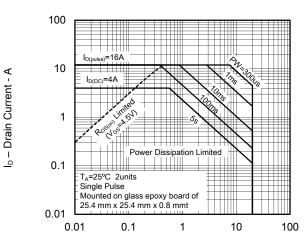
T_A -Ambient Temperature - °C

TOTAL POWER DISSIPATION vs. AMBIENT TEMPERATURE



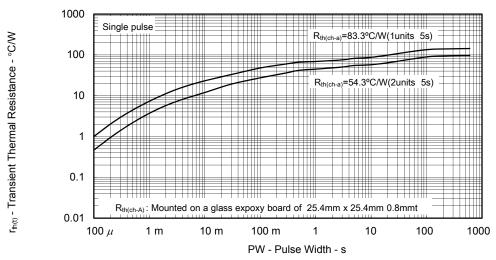
T_A -Ambient Temperature - °C

FORWARD BIAS SAFE OPERATING AREA



 $V_{\text{\scriptsize DS}}$ - Drain to Source Voltage - V

TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH

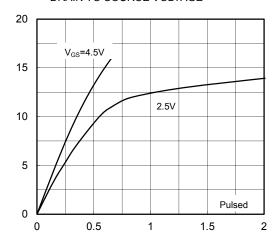


I_D -Drain Current - A

V_{GS(off)} – Gate to Source Cut-off Voltage - V

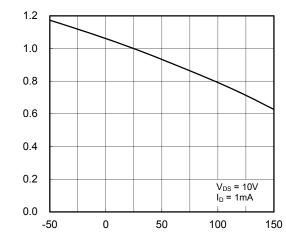
 $R_{\text{DS}(\text{on})}$ - Drain to Source On-state Resistance - $m\Omega$

DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



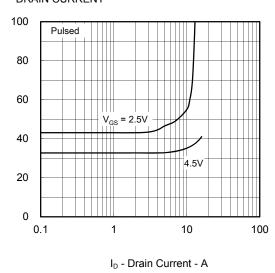
 $V_{\text{\scriptsize DS}}$ - Drain to Source Voltage - V

GATE TO SOURCE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE

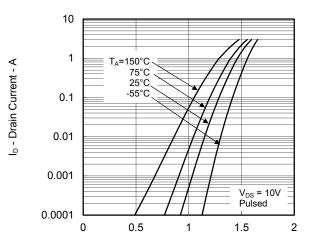


 T_{ch} - Channel Temperature - $^{\circ}C$

DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

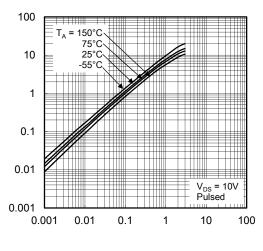


FORWARD TRANSFER CHARACTERISTICS



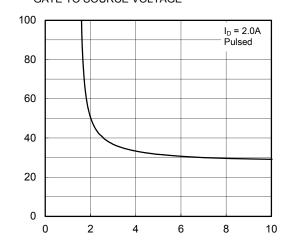
V_{GS} - Gate to Source Voltage - V

FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT



I_D – Drain Current - A

DRAIN TO SOURCE ON-STATE RESISTANCE vs. GATE TO SOURCE VOLTAGE



V_{GS} - Gate to Source Voltage - V

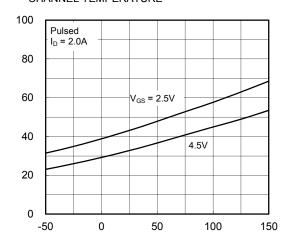
| y_{fs} | - Forward Transfer Admittance - S

R_{DS(on)} – Drain to Source On-state Resistance - mΩ

 $\mathsf{R}_{\mathsf{DS}(\mathsf{on})}\operatorname{-Drain}$ to Source On-state Resistance - $m\Omega$

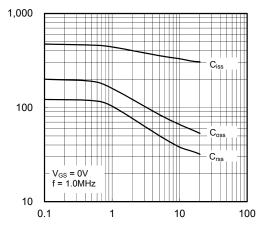
t_{d(on)}, t_f, t_{d(off)}, t_r - Switching Time - Ls

DRAIN TO SOURCE ON-STATE RESISTANCE vs. CHANNEL TEMPERATURE



T_{ch} - Channel Temperature - °C

CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE

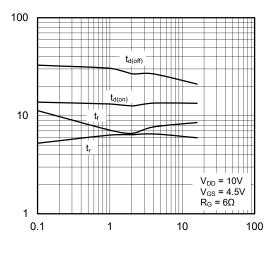


Ciss, Coss, Crss - Capacitance - pF

V_{DS} - Drain to Source Voltage - V

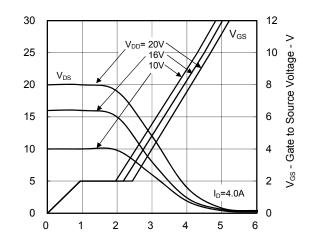
V_{DS} - Drain to Source Voltage - V

SWITCHING CHARACTERISTICS



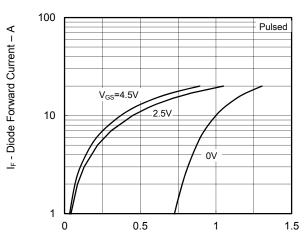
ID - Drain Current - A

DYNAMIC INPUT/OUTPUT CHARACTERISTICS



 $\ensuremath{\mathsf{Q}}_G$ - Gate Charge - nC

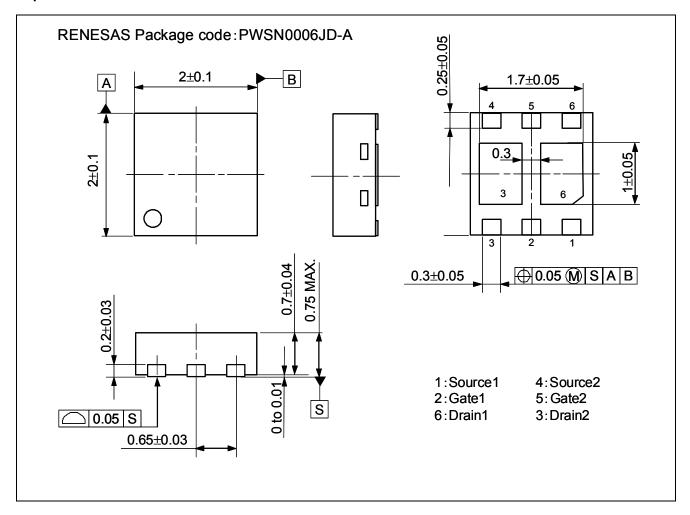
SOURCE TO DRAIN DIODE FORWARD VOLTAGE



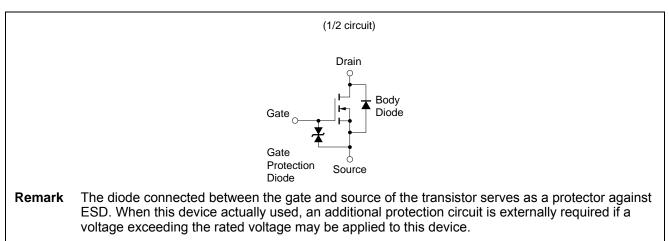
 $V_{F(S\!-\!D)}$ - Drain to Source Voltage - V

Package Drawings (Unit: mm)

6pinHUSON2020



Equivalent Circuit



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